WHAT IS CLAIMED IS:

1. A method for forming a light emitting device, the method comprising:

providing a transparent substrate, on which substrate a transparent anode layer, a light emitting layer, a metal cathode layer are sequentially formed;

forming a sealant layer, at least covering the light emitting layer and the metal cathode layer;

providing a covering layer;

performing an evaporation depositing process, to forming an active absorption layer on the covering layer at a covering surface; and

putting the covering layer, by the covering surface, over at least a portion of the sealant layer above the metal cathode layer.

2. The method of claim 1, wherein before the step of performing the evaporation process, the method further comprises forming a recess region on the covering surface of the covering layer, whereby the active absorption layer is formed on a recessed surface of the recess region.

3. The method of claim 1, wherein in the step of providing the covering layer, the covering layer comprises a cap-like layer to completely cover over the sealant layer, the transparent anode layer, light emitting layer, and the metal cathode layer.

4. The method of claim 3, before the step of performing the evaporation depositing process, further comprising forming a recess region on the covering surface of the covering layer, whereby the active absorption layer is formed on a recessed surface of the recess region.

5. The method of claim 3, wherein there is a clearance between the cap-like covering layer and the sealant layer.

6. The method of claim 1, wherein the metal cathode layer comprises one selected from the group consisting of Li, Mg, and Ca.

7. The method of claim 1, the active absorption layer comprises one selected from the group consisting of Li, Mg, and Ca.

8. A method form forming a light emitting device, the method comprising:

providing a transparent substrate, on which substrate a transparent anode layer, a light emitting layer, a metal cathode layer are sequentially formed;

performing an evaporation deposition process, to form an active absorption layer at least cover the metal cathode layer;

forming a sealant layer, at least covering the light emitting layer and the metal cathode layer;

providing a covering layer; and

putting the covering layer, by the covering surface, over at least a portion of the sealant layer above the metal cathode layer.

9. The method of claim 8, wherein the metal cathode layer comprises one selected from the group consisting of Li, Mg, and Ca.

10. The method of claim 8, the active absorption layer comprises one selected from the group consisting of Li, Mg, and Ca.

11. A method for forming a light emitting device, the method comprising:

providing a transparent substrate, on which substrate a transparent anode layer, a light emitting layer, a metal cathode layer are sequentially formed;

forming an insulating layer over the metal cathode layer;

forming a sealant layer, at least covering the insulating layer, the light emitting layer, the metal cathode layer, and the transparent anode layer;

providing a covering layer; and

putting the covering layer on a portion of the sealant layer above the metal cathode layer.

12. The method of claim 11, wherein the metal cathode layer comprises one selected from the group consisting of Li, Mg, and Ca.

13. The method of claim 11, the active absorption layer comprises one selected from the group consisting of Li, Mg, and Ca.

14. A method for forming a light emitting device, the method comprising:

providing a covering layer;

providing a light emitting unit, comprising a metal cathode layer;

performing an evaporation depositing process, to form an active absorption layer on a surface of the covering layer;

putting the covering layer with the surface having the active absorption layer, over at least a portion of the light emitting unit above the metal cathode layer.

15. The method of claim 14, wherein the metal cathode layer comprises one selected from the group consisting of Li, Mg, and Ca.

16. The method of claim 14, the active absorption layer comprises one selected from the group consisting of Li, Mg, and Ca.

17. A method for forming a light emitting device, the method comprising:

providing a transparent substrate, on which substrate a transparent anode layer, a light emitting layer, a metal cathode layer are sequentially formed;

optionally forming a sealant layer, at least covering the metal cathode layer;

providing a covering layer;

etching the covering layer to form a recess region on the covering layer at a covering surface with respect to the metal cathode layer, and forming a trench enclosing the recess region;

performing an evaporation deposition process, to form an active absorption layer on the covering layer within the recess region;

coating a gluing layer on a portion of the covering layer between the trench and the recess region; and

adhering the covering layer onto the transparent substrate.

18. The method of claim 17, wherein the step of etching covering layer comprises performing a sand-jet etching process.

19. The method of claim 18, wherein the step of etching covering layer comprises performing a sand-jet etching process with etchant of aluminum oxide particles.

20. A method for forming a light emitting device, the method comprising:

providing a transparent substrate, on which substrate a transparent anode layer, a light emitting layer, a metal cathode layer are sequentially formed;

optionally forming a sealant layer, at least covering the light emitting layer and the metal cathode layer;

providing a covering layer;

performing an evaporation deposition process, to form an active absorption layer on the covering layer within the recess region;

forming two frit lines on the covering layer, enclosing the active absorption layer, wherein a clearance between the two frit lines is reserved;

properly dripping a sealant material on the clearance; and

adhering the covering layer on the transparent substrate layer through the sealant material, wherein the active absorption layer is above the metal cathode layer.